L Number	Hits	Search Text	DB	Time stamp
1	32	cROSSLAND-WILLIAM-A.IN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/07 14:58
2	6	cROSSLAND-WILLIAM-A.IN. and ((back adj plane) or (backplane))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/07 14:59
3	5	(cROSSLAND-WILLIAM-A.IN. and ((back adj plane) or (backplane))) and active	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2004/06/07 14:59
4	9	("4643526" | "4682858" | "4826297" | "5381255" | "5644373" | "6151091" | "6236444" | "6373547" | "6486936").PN.	USPAT	2004/06/07 15:01
-	71	kinoshita-masayoshi.in.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 15:59
-	0	depletion adj relm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 15:59
-	765	depletion adj region.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:00
-	1552	backplane.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:00
-	0	(depletion adj region.clm.) and backplane.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:00
-	1548	biassed.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:01
-	5	(depletion adj region.clm.) and biassed.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:02
-	1002998	(adjacent or spaced).clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:07
-	447	(depletion adj region.clm.) and ((adjacent or spaced).clm.)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:09
-	4	((depletion adj region.clm.) and ((adjacent or spaced).clm.)) and biassed.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:13
-	71	((depletion adj region.clm.) and ((adjacent or spaced).clm.)) and diode.clm.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:16
-	2115949	@ad>19981219	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:17
-	59	(((depletion adj region.clm.) and ((adjacent or spaced).clm.)) and diode.clm.) not @ad>19981219	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/14 16:17

-	12	("3463977" | "3978511" | "4127932" | "4137428" | "4326211" | "4383266" | "4616247" | "4631592" | "4779126" | "4805004" | "4816890" | "4866499").PN.	USPAT	2003/05/14 20:45
-	5	"4816890"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 12:06
-	9	"5282018"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 12:24
-	1	"4893160".PN.	USPAT	2003/05/15 12:27
-	19	"4646117"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 12:33
-	1	"6512263"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:22
-	44	("4336603" | "4380057" | "4417264" | "4477825" | "4855955" | "4885719" | "5021999" | "5043940" | "5047362" | "5070032" | "5095344" | "5095461" | "5159570" | "5172338" | "5210047" | "5278439" | "5297148" | "5313421" | "5315341" | "5343063" | "5364806" | "5411905" | "5412600" | "5414693" | "5440158" | "5486714" | "5492846" | "5576567" | "5606521" | "5616510" | "5636160" | "5643814" | "5661053" | "5679591" | "5712180" | "5714412" | "5786612" | "5812449" | "5851879" | "5991201" | "6091633" | "6103573" | "6151248" | "6329685").PN.	USPAT	2003/05/15 12:33
-	33	("4336603" | "4380057" | "4417264" | "4855955" | "5021999" | "5043940" | "5070032" | "5095344" | "5095461" | "5159570" | "5172338" | "5210047" | "5278439" | "5297148" | "5313421" | "5315541" | "5343063" | "5364806" | "5411905" | "5412600" | "5414693" | "5486714" | "5576567" | "5606521" | "5616510" | "5636160" | "5643814" | "5661053" | "5712180" | "5714412" | "5786612" | "5812449" | "5991201" | "B15172338").PN.	USPAT	2003/05/15 12:34
-	9	"5825063"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:24
-	21660	"MEM"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:24
-	22146	"MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:28
-	516	("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:29
-	390	(("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:29

-	384	((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:30
-	257	(((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:31
-	0	((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@ad<=1998)	USPAT; US-PGPUB; EPO; .JPO; IBM_TDB	2003/05/15 14:32
-	0	((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@pd<=1998)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:34
-	0	((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@pd<=2001)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:35
-	180	((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@pd<=20010310)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:35
-	134	(((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@pd<=20010310)) and (@pd<=19981219)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:35
-	0	((((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@pd<=20010310)) and (@pd<=19981219)) and backplane	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 14:36
-	56	((((((("MEM" or ((memory adj device) and (substrate and capacitor) with (under or beneath))) and ((substrate and capacitor) with (under or beneath))) and (source and drain)) and (plate$3 or electrode)) and (word adj line) and (bit adj line)) and (@pd<=20010310)) and (@pd<=19981219)) and address	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 15:03
-	4	("3962713" | "4327476" | "4432006" | "4688063").PN.	USPAT	2003/05/15 14:45
-	5	5237528.URPN.	USPAT	2003/05/15 14:46
-	6	("5155573" | "5166090" | "5237528" | "5455192" | "5795804" | "6018177").PN.	USPAT	2003/05/15 14:48
-	4	("3962713" | "4327476" | "4432006" | "4688063").PN.	USPAT	2003/05/15 14:51

-		4	("3962713" | "4327476" | "4432006" | "4688063").PN.	USPAT	2003/05/15 14:52
-		1	"4786954".PN.	USPAT	2003/05/15 14:57
-		3	("3962713" | "4327476" | "4432006").PN.	USPAT	2003/05/15 14:58
-		3	4901128.URPN.	USPAT	2003/05/15 14:58
-		5	(("4901128") or ("4816890") or ("6512263") or ("5223919") or ("5825063")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 15:06
-		6	"4901128"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 15:22
-		3	("3962713" | "4327476" | "4432006").PN.	USPAT	2003/05/15 15:15
-		1	("5825063").PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/15 15:22
-		7	"5214496"	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/28 11:12
-		5	(("20020185684") or ("6479854") or ("6344413") or ("6251720") or ("6269018")).PN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/05/28 11:13
-		0	semiconductor adj active adj plane	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:01
-		2	semiconductor adj active adj backplane	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:05
-		0	20030174117.URPN.	USPAT	2003/12/16 18:02
-		82	active adj backplane	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:05
-		82	(active adj backplane) not 20030174117.URPN.	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:05
-		80	(active adj backplane) not (semiconductor adj active adj backplane)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:05
-		11	((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:06
-		11	(((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:06
-		11	((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:06
-		8	(((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:07

-	6	(((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:26
-	45	("4090219" | "4508429" | "4634226" | "4709995" | "4864290" | "4969119" | "4976515" | "4978952" | "5011269" | "5061049" | "5083857" | "5093652" | "5096279" | "5122791" | "5128782" | "5170156" | "5178445" | "5189406" | "5192946" | "5206629" | "5214420" | "5225823" | "5233447" | "5254980" | "5255100" | "5278652" | "5280277" | "5287096" | "5303055" | "5339090" | "5339116" | "5359345" | "5365283" | "5436742" | "5448314" | "5465168" | "5483307" | "5497172" | "5499062" | "5506597" | "5523803" | "5548301" | "5589852" | "5606342" | "5705424").PN.	USPAT	2003/12/16 18:12
-	0	6570550.URPN.	USPAT	2003/12/16 18:13
-	2	(((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:27
-	2	(((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and'transistor))) and (address$4 and (active adj element))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:29
-	42	(((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:34

–		0	((((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4))) and (conduct$4 with metal)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:30
–		21	((((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4))) and (conduct$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:30
–		12	((((((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4))) and (conduct$4)) and (dop$5 or deplet$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:32

–	9	(((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4)) and (conduct$4)) not ((((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4)) and (conduct$4)) and (dop$5 or deplet$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:32
–	18	("3992686" | "4158220" | "4241381" | "4450029" | "4717344" | "4719541" | "4755145" | "4862326" | "5023754" | "5136470" | "5162977" | "5185502" | "5233677" | "5287244" | "5390081" | "5528464" | "5617299" | "5659245").PN.	USPAT	2003/12/16 18:33
–	40	(active adj backplane) not ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4)))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:35

–		15	((active adj backplane) not ((((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4)))) and transistor	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/16 18:37
–		7	("4229095" | "5177437" | "5475513" | "5555035" | "5587829" | "6016224" | "6348990").PN.	USPAT	2003/12/16 18:36
–		25	((active adj backplane) not ((((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4)))) not (((active adj backplane) not ((((active adj backplane) not (semiconductor adj active adj backplane)) not ((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) or (((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) not ((((((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor)) and (activ$4 or energi$4)) and electrode) and (capacit$4)) and diode)) or ((((active adj backplane) not (semiconductor adj active adj backplane)) not (((active adj backplane) not (semiconductor adj active adj backplane)) and (pixel and transistor))) and (address$4 and (active adj element)))) and (address$4)))) and transistor)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:57

-	283	(Active adj matrix) and (backplane)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:57
-	167	((Active adj matrix) and (backplane)) and electrode and array	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:58
-	151	(((Active adj matrix) and (backplane)) and electrode and array) and (substrate)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:58
-	54	((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:59
-	0	(((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (charge$4 near3 miplant)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:59
-	0	(((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (charge$4 near3 implant)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 13:59
-	1	(((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (charge$4 near3 trap$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:02
-	0	((((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (capacit$4)) and (gurad adj ring)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:03
-	0	((((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (capacit$4)) and (guard adj ring)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:03
-	0	((((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (capacit$4)) and (depletion adj region)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:03
-	2	((((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (capacit$4)) and ((bit adj line) and (word adj line))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:04
-	34	(((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (capacit$4)	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:42
-	0	20030222315.URPN.	USPAT	2003/12/17 14:21
-	20	(((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) not ((((((Active adj matrix) and (backplane)) and electrode and array) and (substrate)) and (deplet$4 or dop$4)) and (capacit$4))	USPAT; US-PGPUB; EPO; JPO; IBM_TDB	2003/12/17 14:42

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